

# NPN SILICON RF POWER TRANSISTOR

**DESCRIPTION:**

The **ASI AVF100** is Designed for

**FEATURES:**

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- **Omnigold™** Metalization System

**MAXIMUM RATINGS**

<b>I<sub>C</sub></b>	10 A
<b>V<sub>CB</sub></b>	60 V
<b>V<sub>CE</sub></b>	35 V
<b>P<sub>DISS</sub></b>	140 W @ T <sub>C</sub> = 25 °C
<b>T<sub>J</sub></b>	-65 °C to +200 °C
<b>T<sub>STG</sub></b>	-65 °C to +150 °C
<b>θ<sub>JC</sub></b>	35 °C/W

**PACKAGE STYLE .250 2L FLG (B)**

DIM	MINIMUM inches / mm	MAXIMUM inches / mm
A	.095 / 2.41	.105 / 2.67
B	1.050 / 26.67	
C	.245 / 6.22	.255 / 6.48
D	.120 / 3.05	.140 / 3.56
E	.552 / 14.02	.572 / 14.53
F	.790 / 20.07	.810 / 20.57
G		.285 / 7.24
H	.003 / 0.08	.007 / 0.18
I	.052 / 1.32	.072 / 1.83
J	.120 / 3.05	.130 / 3.30
K		.210 / 5.33

**ORDER CODE: ASI10569**

**CHARACTERISTICS** T<sub>C</sub> = 25 °C

SYMBOL	TEST CONDITIONS	MINIMUM	TYPICAL	MAXIMUM	UNITS
<b>BV<sub>CEO</sub></b>	I <sub>C</sub> = 50 mA	35			<b>V</b>
<b>BV<sub>CER</sub></b>	I <sub>C</sub> = 50 mA      R <sub>BE</sub> = 10 Ω	60			<b>V</b>
<b>BV<sub>EBO</sub></b>	I <sub>E</sub> = 10 mA	4.0			<b>V</b>
<b>I<sub>CES</sub></b>	V <sub>E</sub> = 28 V			5	<b>mA</b>
<b>h<sub>FE</sub></b>	V <sub>CE</sub> = 5.0 V      I <sub>C</sub> = 1.0 A	10		100	<b>---</b>
<b>C<sub>ob</sub></b>	V <sub>CB</sub> = 28 V      f = 1.0 MHz			80	<b>pF</b>
<b>P<sub>G</sub></b> <b>η<sub>c</sub></b>	V <sub>CC</sub> = 40 V    P <sub>OUT</sub> = 100 W    f = 1030 - 1090 MHz	10 35			<b>dB</b> <b>%</b>